



ATTACHMENT A

REMARKS

A number of rejections have been made under 35 USC 112. Considering the specific objections raised, claim 2 has been amended to overcome the objection raised with respect to the recitation "growth temperature" in line 1.

With respect to claim 3, it is not seen that the recitations "Gallium Nitride" and "Aluminum Nitride" in line 2 require the insertion of the word -- a -- before the composition in question. This was not required in, for example, claim 1, wherein "Indium Nitride" is recited in the first line and, more generally, it is not necessary to add an -- a -- before a chemical composition in the same way that it is not necessary to refer to "a Aluminum" or "a Gold."

With respect to claim 6, this claim has also been amended to address the issue raised.

Finally, with regard to claim 7, the terminology "and/or" has been eliminated and replaced by more appropriate terminology.

Claims 1-10 have been rejected as being "unpatentable over the Briot, et al reference entitled 'Indium nitride quantum dots grown by metalorganic vapor phase epitaxy'." It is respectfully submitted that the "Briot, et al reference" is not an effective reference against the present application. The present application claims a priority date of provisional application 60/493,452 filed on August 8, 2003, which is, of course, prior to the "6 October 2003" publication date of the Briot, et al reference. In fact, the provisional application includes the "Briot, et al reference" as part thereof. Hence, it is respectfully submitted that the rejection of claims 1-10 based on the Briot, et al reference should be withdrawn.

Allowance of the application in its present form is respectfully solicited.

END REMARKS